

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
100V	3.3mΩ@10V	180A

### Feature

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low RDS(ON)

### Application

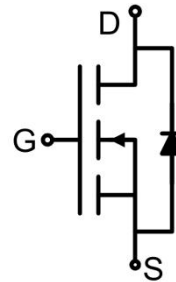
- DC/DC Converter
- Power switching application
- Uninterruptible power supply

### Package

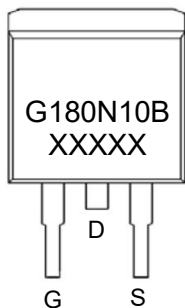


TO-263AB

### Circuit diagram



### Marking



### Absolute maximum ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current (T <sub>C</sub> =25°C)	I <sub>D</sub>	180	A
Continuous Drain Current (T <sub>C</sub> =100°C)	I <sub>D</sub> (100°C)	113	A
Pulsed Drain Current <sup>1)</sup>	I <sub>DM</sub>	720	A
Power Dissipation <sup>3)</sup>	P <sub>D</sub>	2.7	W
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	0.5	°C/W
Single pulse avalanche energy <sup>2)</sup>	E <sub>AS</sub>	1024	mJ
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### Electrical characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	100			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A		2.5	3.3	mΩ
<b>Dynamic characteristics<sup>4)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz		8900		pF
Output Capacitance	C <sub>oss</sub>			2750		
Reverse Transfer Capacitance	C <sub>rss</sub>			65		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 90A		122		nC
Gate-Source Charge	Q <sub>gs</sub>			37		
Gate-Drain Charge	Q <sub>gd</sub>			29		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 90A, R <sub>GEN</sub> = 2.2Ω		25		nS
Turn-on rise time	t <sub>r</sub>			194		
Turn-off delay time	t <sub>d(off)</sub>			52		
Turn-off fall time	t <sub>f</sub>			13		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current	I <sub>S</sub>				180	A
Diode Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 50A			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 90A, di/dt = 400A/μs		56		nS
Reverse Recovery Charge	Q <sub>rr</sub>			317		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature.
- 2) T<sub>J</sub> = 25°C, V<sub>DD</sub> = 50V, V<sub>G</sub> = 10V, R<sub>G</sub> = 25Ω, L = 2mH, I<sub>AS</sub> = 32A.
- 3) P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.
- 4) Guaranteed by design, not subject to production testing.

## Typical Characteristics

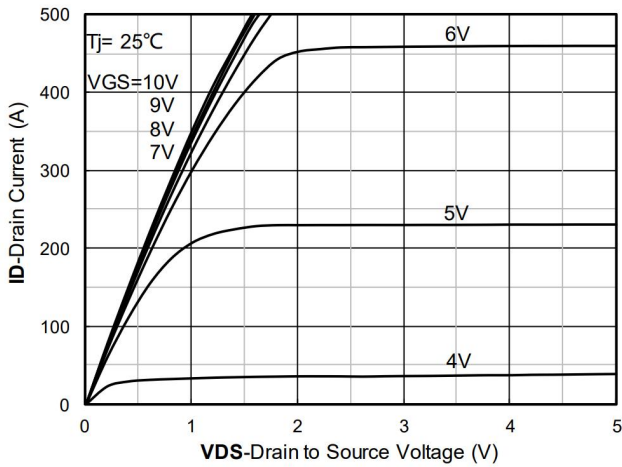


Figure 1. Output Characteristics

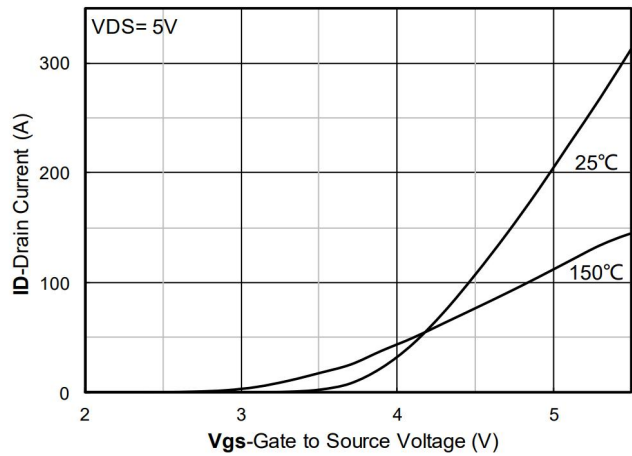


Figure 2. Transfer Characteristics

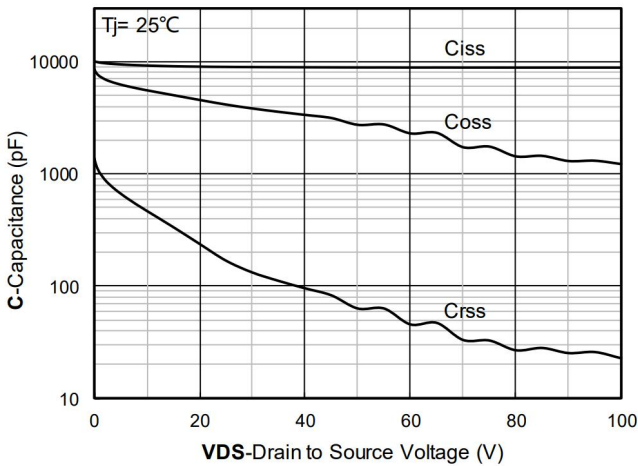


Figure 3. Capacitance Characteristics

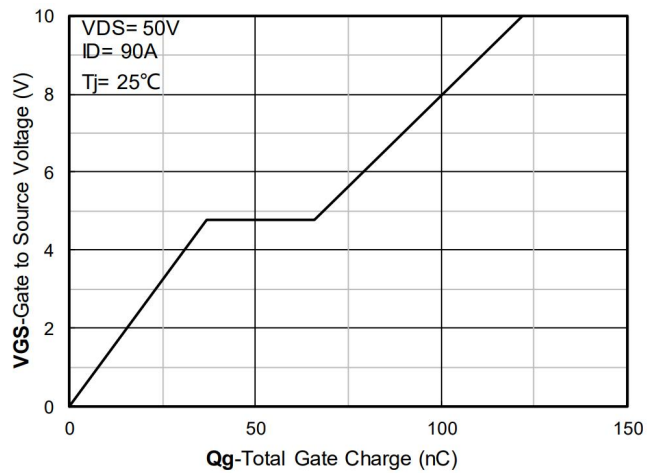


Figure 4. Gate Charge

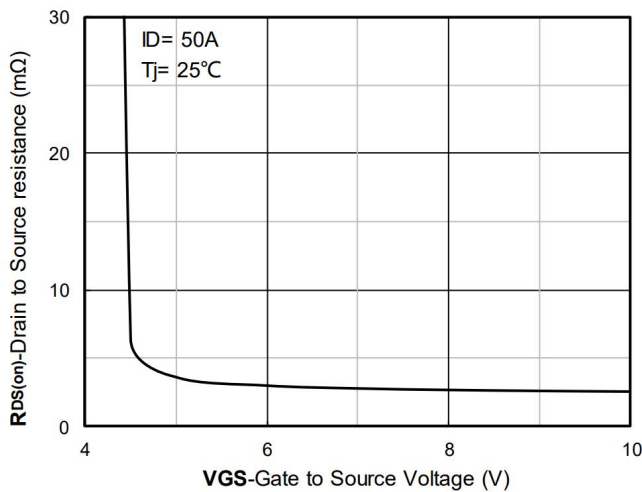


Figure 5. On-Resistance vs Gate to Source Voltage

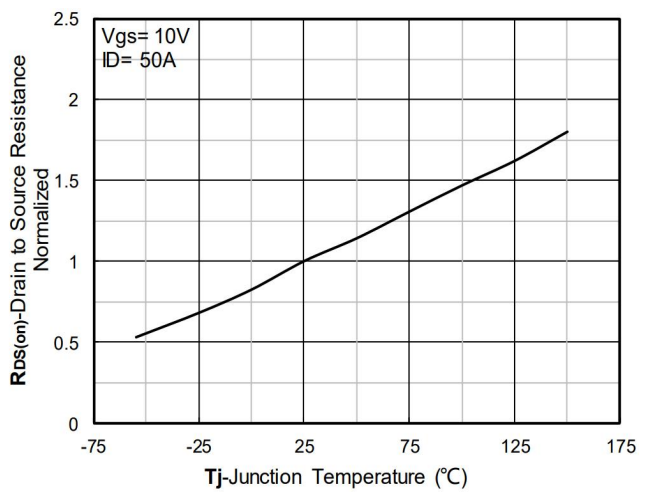


Figure 6. Normalized On-Resistance

## Typical Characteristics

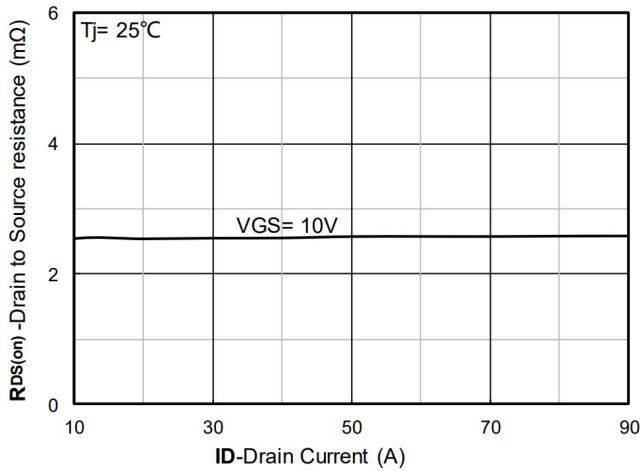


Figure 7. RDS(on) VS Drain Current

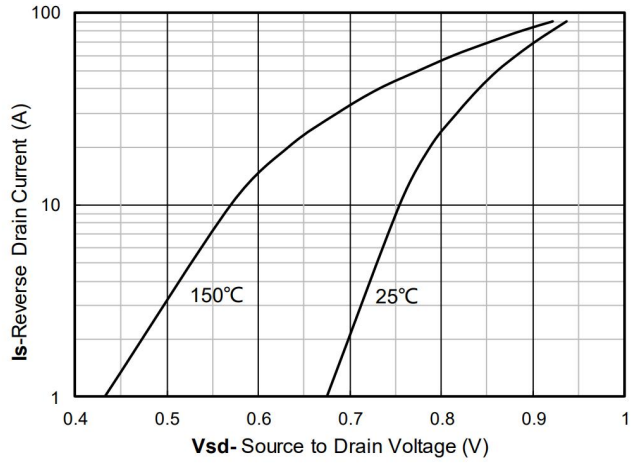


Figure 8. Forward characteristics of reverse diode

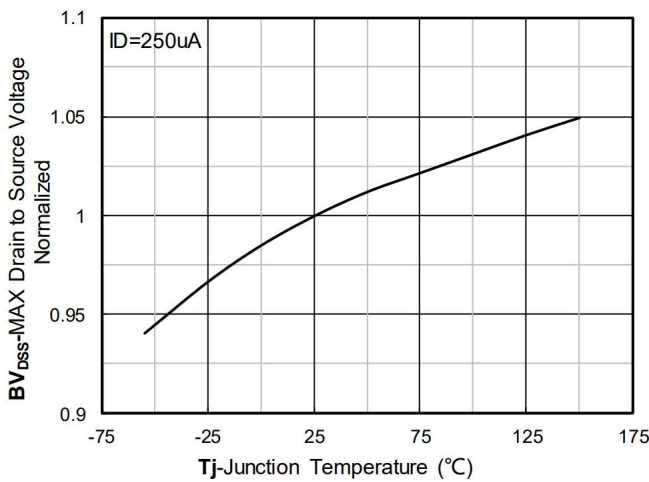


Figure 9. Normalized breakdown voltage

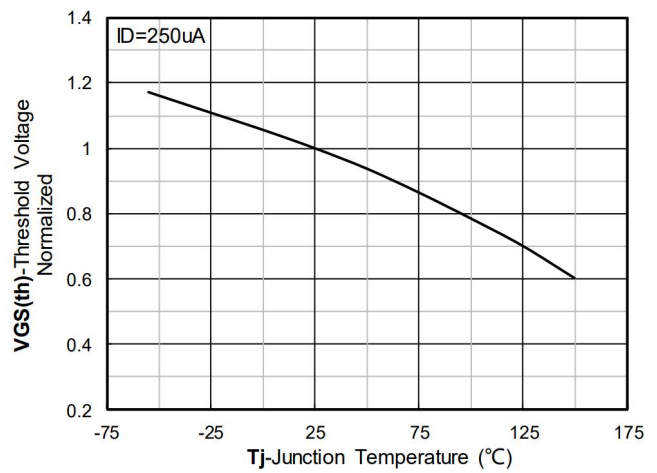


Figure 10. Normalized Threshold voltage

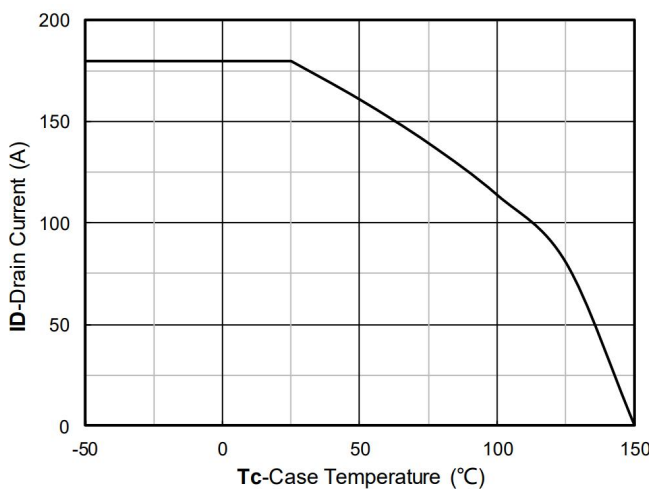


Figure 11. Current dissipation

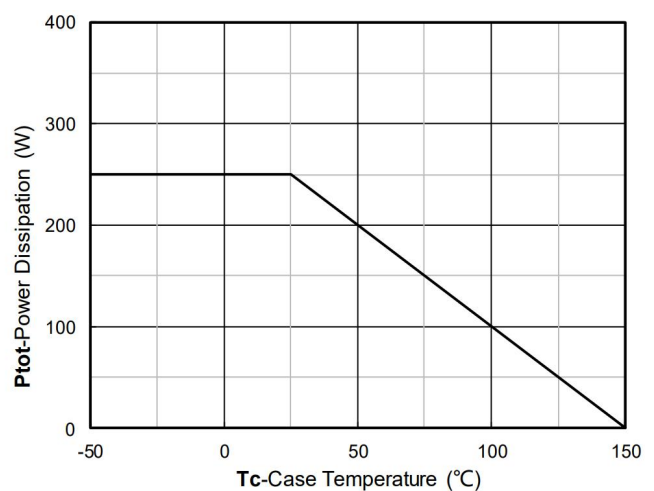


Figure 12. Power dissipation

## Typical Characteristics

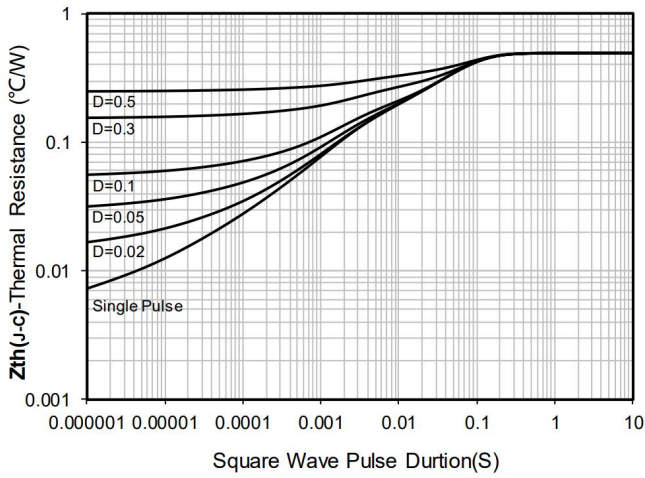


Figure 13. Maximum Transient Thermal Impedance

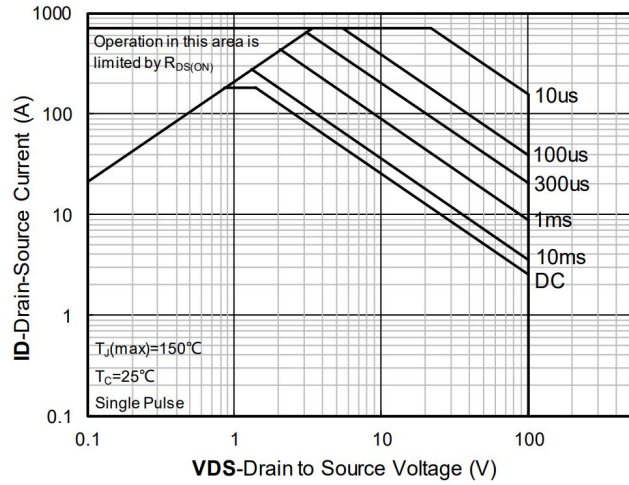
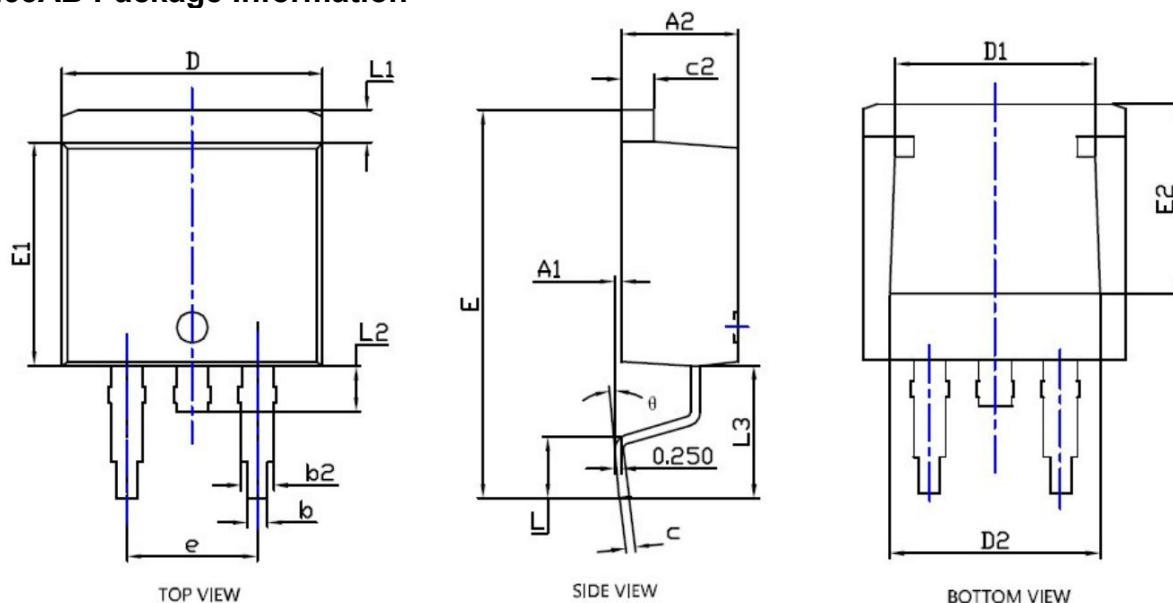


Figure 14. Safe Operation Area

### TO-263AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A1	0.000	0.250	0.000	0.010
A2	4.430	4.730	0.174	0.186
b	0.720	0.920	0.028	0.036
b2	1.180	1.380	0.046	0.054
c	0.330	0.450	0.013	0.018
c2	1.220	1.340	0.048	0.053
D	10.000	10.300	0.394	0.406
D1	7.500	8.100	0.295	0.319
D2	7.700	8.300	0.303	0.327
E	14.500	15.500	0.571	0.610
E1	8.550	8.850	0.337	0.348
E2	7.000	7.600	0.276	0.299
e	5.080 BSC		0.200 BSC	
L	1.790	2.790	0.070	0.110
L1	1.120	1.420	0.044	0.056
L2	0.770	1.770	0.030	0.070
L3	5.000 REF		0.197 REF	
$\theta$	0°	8°	0°	8°